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18309 float\$3 near\$ gate\$1 USPAT; USPGPUB; PO	-	0,,,,	The state of the s		2003/00/10 10:21
2					
Select\$3 near2 gate\$1 US-PGPUB; PO USPAT;	2	18309	float\$3 near3 gate\$1		2003/06/10 10:22
3 56191 control near2 gate\$1 USPAT; USPAPPUB; PO					
3 56191 control near2 gate\$1 USPAT; USPGPUB; PO USPAT; USPGPUB					
4	3	56191	control near2 gate\$1		2003/06/10 10:22
25443 select\$3 near2 gate\$1 PO USPAT, US-PGPUB; PO USPAT			Source Proof.		2003/00/10 10:22
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1754026 1754	4	25443	select\$3 near2 gate\$1		2003/06/10 10:22
Po			B		2000,00,10 10.22
Description					
1754026 1754026 (non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or poly-si or poly-si or goly-systalline adj (si or silicon))) USPAT, USPGPUB, IPO	5	95088	polysilicon or polysi or poly-si or (polycrystalline adi (si or silicon))		2003/06/10 10:23
A A A A A A A A A A			Francisco es Frañas es Frañas es (Frañas) estama mel (es es assesses))		2005/00/10 10:25
Control near2 gate\$1) and (polysilicon or polysi or polysi or polysi or polysi or polysion or polysi or polysion or polysi or polysion polysion or p					
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1754026 (polycrystalline adj (si or silicon))) Source\$1 or drain\$1 USPAT; USPGPUB; IPO USPAT; USPGPU					2000100110110120
1754026				-	
Section Sect	7	1754026			2003/06/10 10:23
8					
10					
and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1) 10 132929	8	4175	((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1)		2003/06/10 10:24
9 301054 etch\$3 (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1) JPO USPAT; US-PGPUB; IPO USPAT; US-PGPUB;				,	
10 132929 implant\$3 US-PGPUB; IPO USPAT; US-PGPUB; IPO US				JPO	
10	9	301054	etch\$3	USPAT;	2003/06/10 10:24
10				US-PGPUB;	
11 1948 ((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or polysi or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3 ((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or polysi or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (select\$3 near2 gate\$1) 27 3543 eras\$3 near2 gate\$1 USPAT; US-PGPUB; JPO US					
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11	ŀ			US-PGPUB;	
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etch\$3 and implant\$3) and (select\$3 near2 gate\$1) 28					
28 161024 polish\$3 or cmp 29 750 (((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1) 30 634 (((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1) 31 309 ((((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon))) and (source\$1 or drain\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or drain\$1) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1) not (((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1) and implant\$3)				ЈРО	
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29 750 ((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (select\$3 near2 gate\$1) ((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1) 30 309 (((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) (((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 (USPAT; gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1) not (((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and (control near2 gate\$1) and (polysilicon or polysi or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and (control near2 gate\$1) and (polysilicon or polysi or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3)					
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or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (select\$3 near2 gate\$1) ((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1) (((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)) not (((((non-volatile or nonvolatile near5 memor\$3)) and (float\$3 near3 gate\$1) and (control near2 gate\$1)) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon))))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (polysilicon or polysi or (polycrystalline adj (si or silicon))))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3)	29	/30			2003/06/10 12:17
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or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)) not ((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3)					
etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)) not (((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3)				1	
or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3)	1				
near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3)					
(si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3)				-	
and (select33 near2 gate31))			and (select\$3 near2 gate\$1))		
	31	309	gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)) not (((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3)	US-PGPUB;	2003/00/10 12:1/

32	61	(polish\$3 or cmp) and ((((((non-volatile or nonvolatile near5 memor\$3)	USPAT;	2003/06/10 12:17
		and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or	US-PGPUB;	
		polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or	JPO	
		drain\$1)) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)) not		
		(((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3		
		gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si		
		or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and		
		etch\$3 and implant\$3) and (select\$3 near2 gate\$1)))		
33	248	((((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3	USPAT;	2003/06/10 12:22
		gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si	US-PGPUB;	
	1	or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and	JPO	
		etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)) not (((((non-volatile		
		or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control		
	1	near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj		
	i :	(si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3)		
		and (select\$3 near2 gate\$1))) not ((polish\$3 or cmp) and		
		((((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3		
		gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si		
		or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and		
		etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)) not (((((non-volatile		
		or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control		
		near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj		
		(si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3)		
		and (select\$3 near2 gate\$1))))		